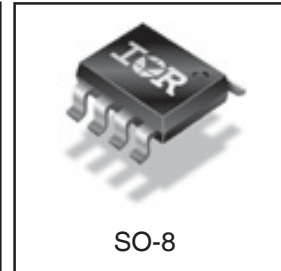
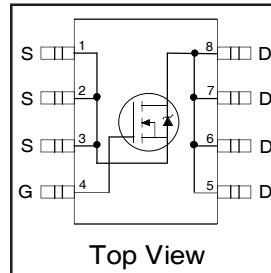


HEXFET® Power MOSFET

$V_{DS}$	<b>100</b>	<b>V</b>
$R_{DS(on) \max}$ (@ $V_{GS} = 10V$ )	<b>26</b>	<b>m<math>\Omega</math></b>
$Q_g$ (typical)	<b>61</b>	<b>nC</b>
$I_D$ (@ $T_A = 25^\circ C$ )	<b>6.9</b>	<b>A</b>



**Features**

Industry-standard pinout SO-8 Package
Compatible with Existing Surface Mount Techniques
RoHS Compliant, Halogen-Free
MSL1, Industrial qualification



**Benefits**

Multi-Vendor Compatibility
Easier Manufacturing
Environmentally Friendlier
Increased Reliability

Base Part Number	Package Type	Standard Pack		Orderable Part Number
		Form	Quantity	
IRF7473PbF-1	SO-8	Tube/Bulk	95	IRF7473PbF-1
		Tape and Reel	4000	IRF7473TRPbF-1

**Absolute Maximum Ratings**

	Parameter	Max.	Units
$I_D @ T_A = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	6.9	A
$I_D @ T_A = 70^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	5.5	
$I_{DM}$	Pulsed Drain Current ①	55	
$P_D @ T_A = 25^\circ C$	Power Dissipation	2.5	W
	Linear Derating Factor	0.02	W/°C
$V_{GS}$	Gate-to-Source Voltage	± 20	V
dv/dt	Peak Diode Recovery dv/dt ②	5.8	V/ns
$T_J$	Operating Junction and	-55 to + 150	°C
$T_{STG}$	Storage Temperature Range		
	Soldering Temperature, for 10 seconds		

**Thermal Resistance**

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JL}$	Junction-to-Drain Lead	—	20	°C/W
$R_{\theta JA}$	Junction-to-Ambient ④	—	50	

Notes ① through ④ are on page 8

**Static @ T<sub>J</sub> = 25°C (unless otherwise specified)**

	Parameter	Min.	Typ.	Max.	Units	Conditions
V <sub>(BR)DSS</sub>	Drain-to-Source Breakdown Voltage	100	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA
ΔV <sub>(BR)DSS</sub> /ΔT <sub>J</sub>	Breakdown Voltage Temp. Coefficient	—	0.11	—	V/°C	Reference to 25°C, I <sub>D</sub> = 1mA ③
R <sub>DS(on)</sub>	Static Drain-to-Source On-Resistance	—	22	26	mΩ	V <sub>GS</sub> = 10V, I <sub>D</sub> = 4.1A ③
V <sub>GS(th)</sub>	Gate Threshold Voltage	3.5	—	5.5	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
I <sub>DSS</sub>	Drain-to-Source Leakage Current	—	—	1.0	μA	V <sub>DS</sub> = 95V, V <sub>GS</sub> = 0V
		—	—	250		V <sub>DS</sub> = 80V, V <sub>GS</sub> = 0V, T <sub>J</sub> = 150°C
I <sub>GSS</sub>	Gate-to-Source Forward Leakage	—	—	100	nA	V <sub>GS</sub> = 20V
	Gate-to-Source Reverse Leakage	—	—	-100		V <sub>GS</sub> = -20V

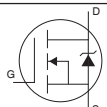
**Dynamic @ T<sub>J</sub> = 25°C (unless otherwise specified)**

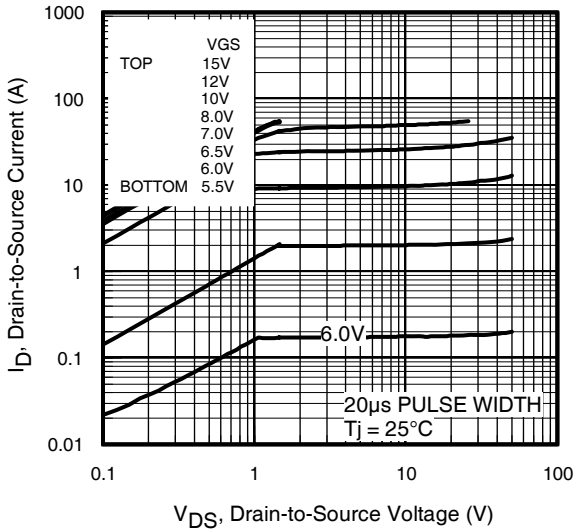
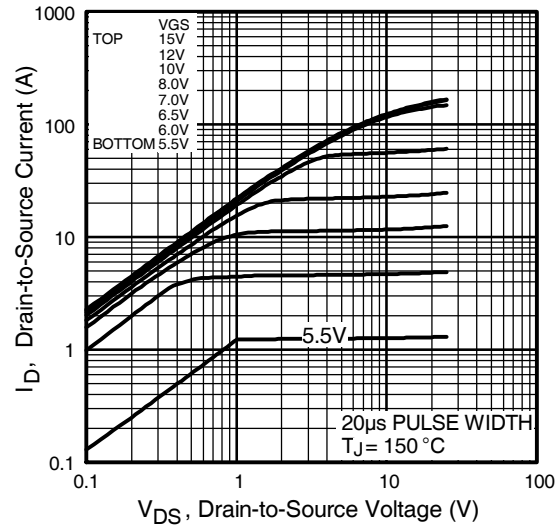
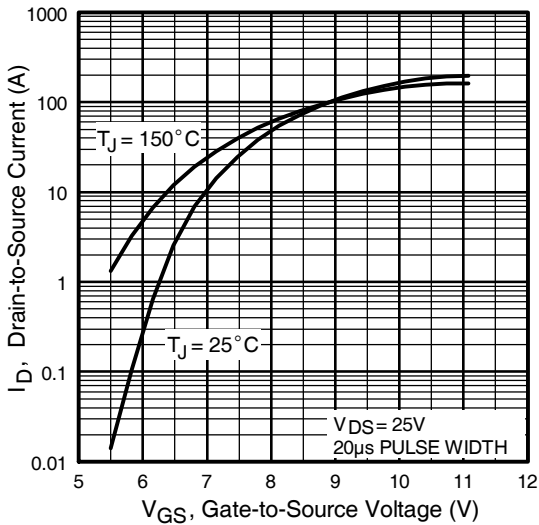
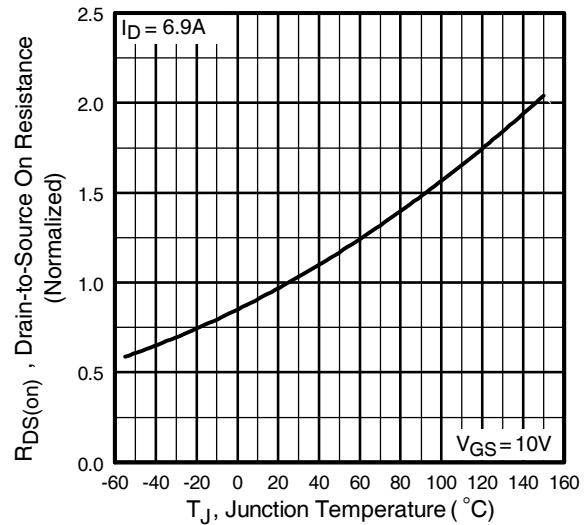
	Parameter	Min.	Typ.	Max.	Units	Conditions
g <sub>fs</sub>	Forward Transconductance	10	—	—	S	V <sub>DS</sub> = 50V, I <sub>D</sub> = 4.1A
Q <sub>g</sub>	Total Gate Charge	—	61	—	nC	I <sub>D</sub> = 4.1A
Q <sub>gs</sub>	Gate-to-Source Charge	—	21	—		V <sub>DS</sub> = 50V
Q <sub>gd</sub>	Gate-to-Drain ("Miller") Charge	—	19	—		V <sub>GS</sub> = 10V,
t <sub>d(on)</sub>	Turn-On Delay Time	—	24	—	ns	V <sub>DD</sub> = 50V
t <sub>r</sub>	Rise Time	—	20	—		I <sub>D</sub> = 4.1A
t <sub>d(off)</sub>	Turn-Off Delay Time	—	29	—		R <sub>G</sub> = 6.0Ω
t <sub>f</sub>	Fall Time	—	11	—		V <sub>GS</sub> = 10V ③
C <sub>iss</sub>	Input Capacitance	—	3180	—	pF	V <sub>GS</sub> = 0V
C <sub>oss</sub>	Output Capacitance	—	230	—		V <sub>DS</sub> = 25V
C <sub>rss</sub>	Reverse Transfer Capacitance	—	120	—		f = 1.0MHz
C <sub>oss</sub>	Output Capacitance	—	830	—		V <sub>GS</sub> = 0V, V <sub>DS</sub> = 1.0V, f = 1.0MHz
C <sub>oss</sub>	Output Capacitance	—	150	—		V <sub>GS</sub> = 0V, V <sub>DS</sub> = 80V, f = 1.0MHz
C <sub>oss eff.</sub>	Effective Output Capacitance	—	230	—		V <sub>GS</sub> = 0V, V <sub>DS</sub> = 0V to 80V ③

**Avalanche Characteristics**

	Parameter	Typ.	Max.	Units
E <sub>AS</sub>	Single Pulse Avalanche Energy②	—	140	mJ
I <sub>AR</sub>	Avalanche Current①	—	4.1	A

**Diode Characteristics**

	Parameter	Min.	Typ.	Max.	Units	Conditions
I <sub>S</sub>	Continuous Source Current (Body Diode)	—	—	2.3	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I <sub>SM</sub>	Pulsed Source Current (Body Diode) ①	—	—	55		
V <sub>SD</sub>	Diode Forward Voltage	—	—	1.3	V	T <sub>J</sub> = 25°C, I <sub>S</sub> = 4.1A, V <sub>GS</sub> = 0V ③
t <sub>rr</sub>	Reverse Recovery Time	—	55	—	ns	T <sub>J</sub> = 25°C, I <sub>F</sub> = 4.1A
Q <sub>rr</sub>	Reverse Recovery Charge	—	140	—	nC	di/dt = 100A/μs ③


**Fig 1.** Typical Output Characteristics

**Fig 2.** Typical Output Characteristics

**Fig 3.** Typical Transfer Characteristics

**Fig 4.** Normalized On-Resistance Vs. Temperature

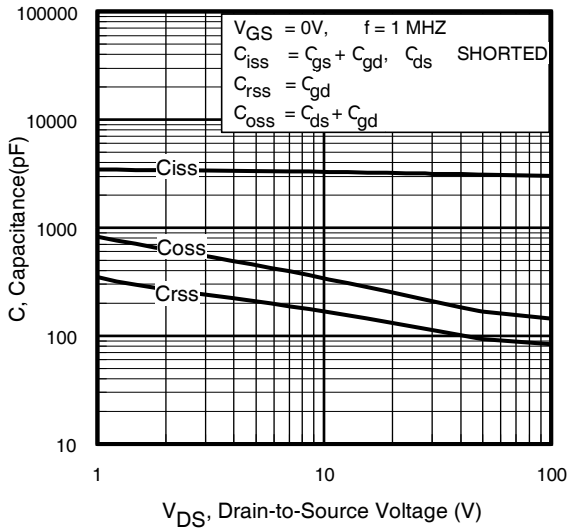


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

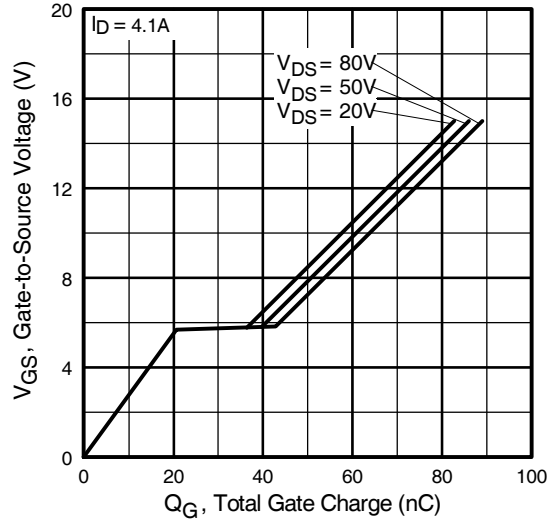


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

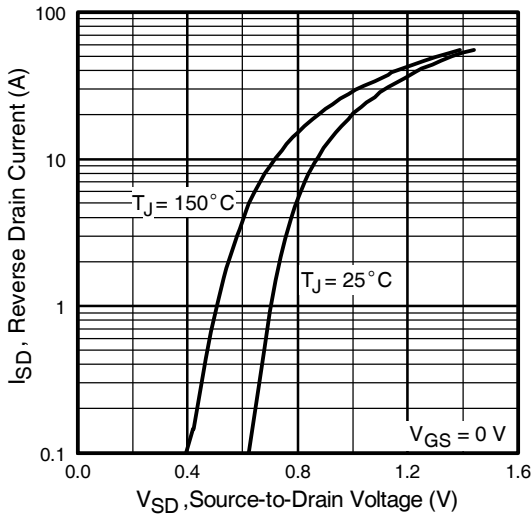


Fig 7. Typical Source-Drain Diode Forward Voltage

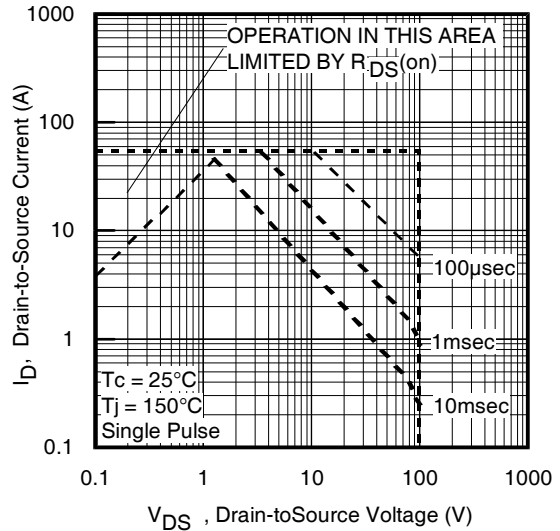
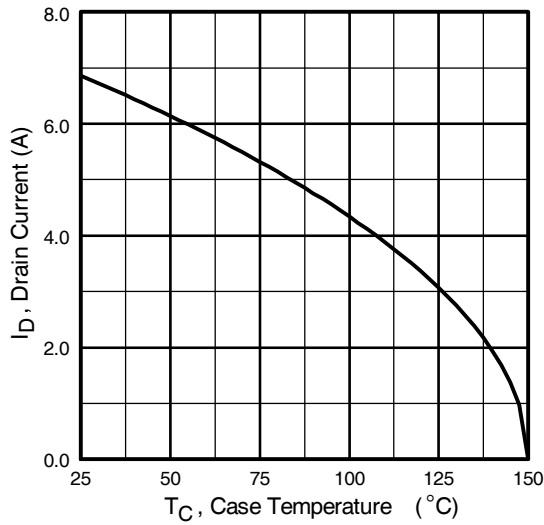
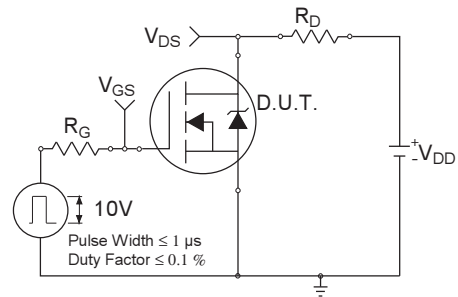


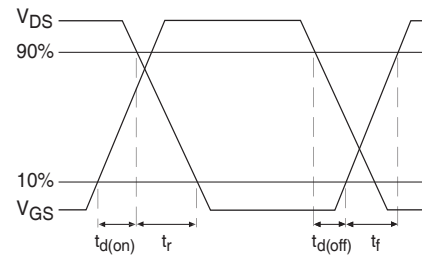
Fig 8. Maximum Safe Operating Area



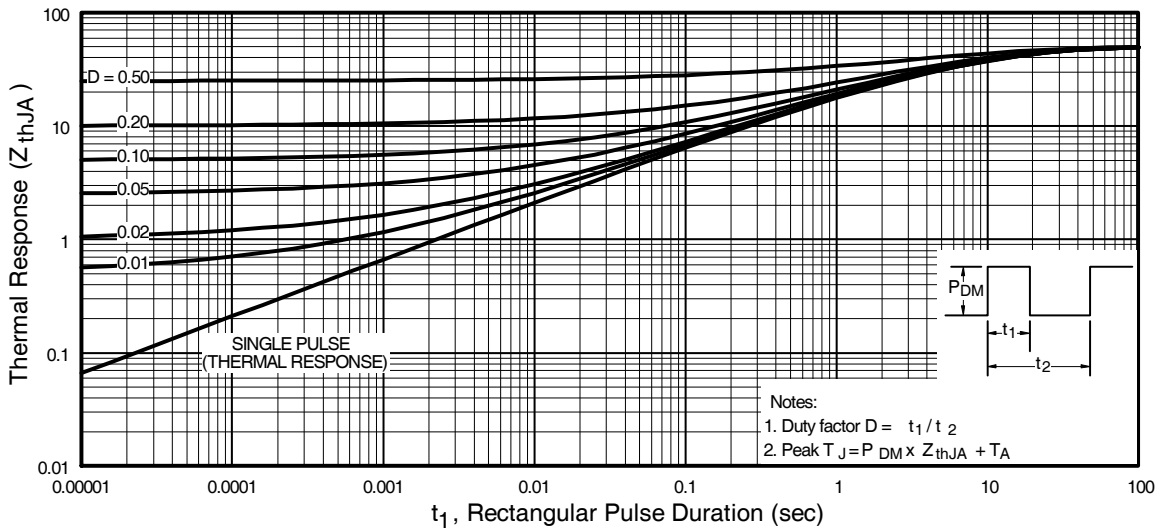
**Fig 9.** Maximum Drain Current Vs. Ambient Temperature



**Fig 10a.** Switching Time Test Circuit



**Fig 10b.** Switching Time Waveforms



**Fig 11.** Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

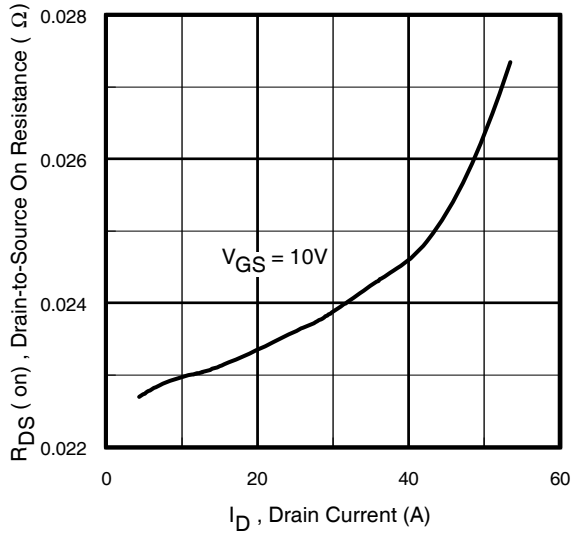


Fig 12. On-Resistance Vs. Drain Current

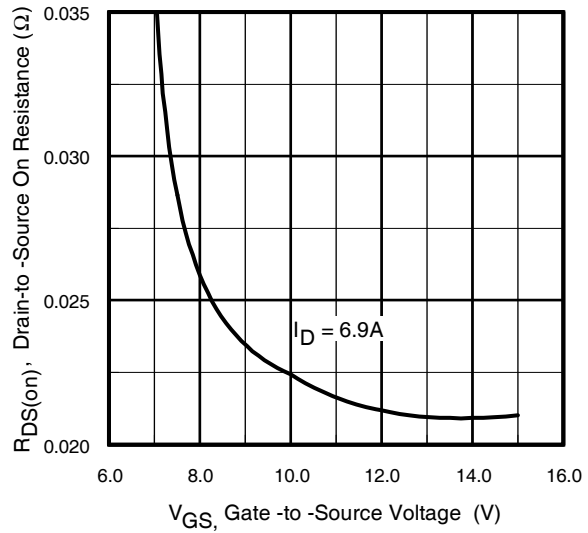


Fig 13. On-Resistance Vs. Gate Voltage

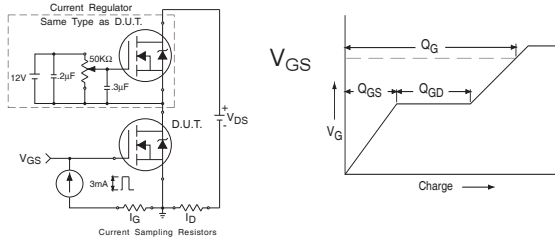


Fig 14a&b. Basic Gate Charge Test Circuit and Waveform

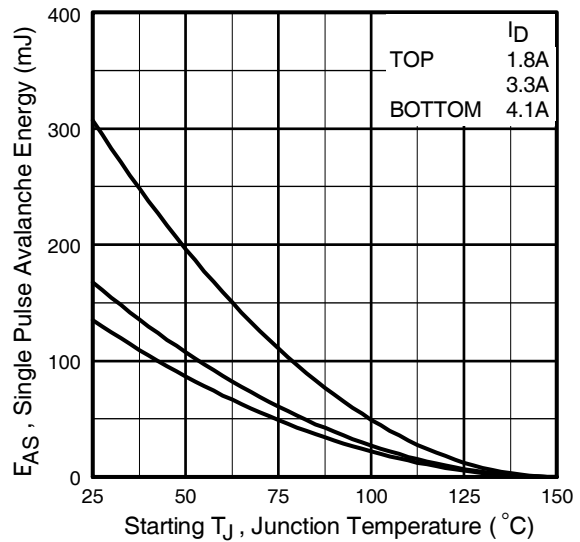


Fig 15c. Maximum Avalanche Energy Vs. Drain Current

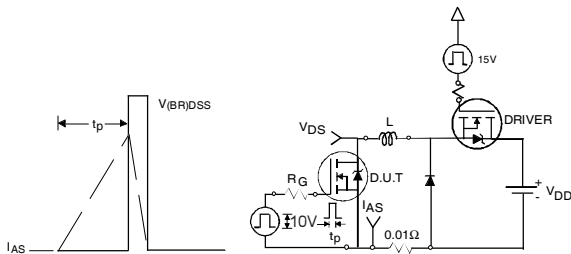
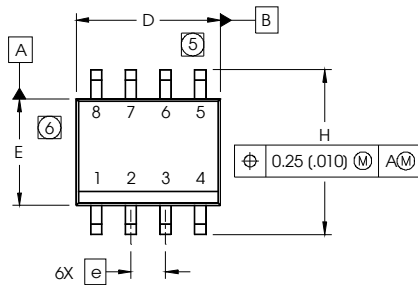


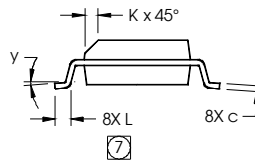
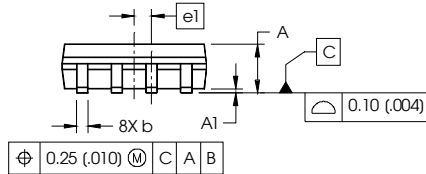
Fig 15a&b. Unclamped Inductive Test circuit and Waveforms

## SO-8 Package Outline (MOSFET & Fetky)

Dimensions are shown in millimeters (inches)



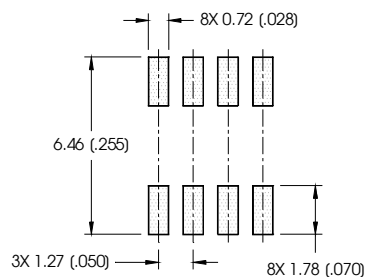
DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.0532	.0688	1.35	1.75
A1	.0040	.0098	0.10	0.25
b	.013	.020	0.33	0.51
c	.0075	.0098	0.19	0.25
D	.189	.1968	4.80	5.00
E	.1497	.1574	3.80	4.00
e	.050 BASIC		1.27 BASIC	
e1	.025 BASIC		0.635 BASIC	
H	.2284	.2440	5.80	6.20
K	.0099	.0196	0.25	0.50
L	.016	.050	0.40	1.27
y	0°	8°	0°	8°



**NOTES:**

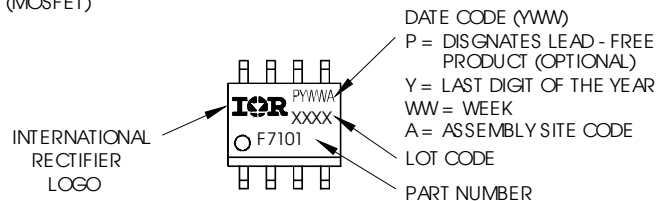
1. DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
2. CONTROLLING DIMENSION: MILLIMETER
3. DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
4. OUTLINE CONFORMS TO JEDEC OUTLINE MS-012AA.
- ⑤ DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.15 (.006).
- ⑥ DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.25 (.010).
- ⑦ DIMENSION IS THE LENGTH OF LEAD FOR SOLDERING TO A SUBSTRATE.

**FOOTPRINT**

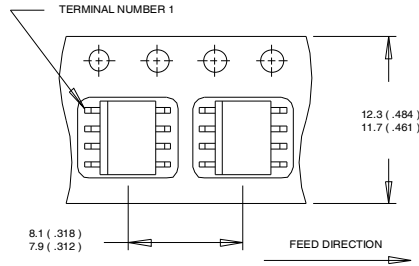


## SO-8 Part Marking Information

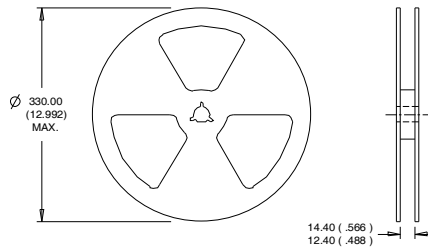
EXAMPLE: THIS IS AN IRF7101 (MOSFET)



**Note:** For the most current drawing please refer to IR website at: <http://www.irf.com/package/>

**SO-8 Tape and Reel** (Dimensions are shown in millimeters (inches))


- NOTES:
1. CONTROLLING DIMENSION - MILLIMETER.
  2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS(INCHES).
  3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



- NOTES:
1. CONTROLLING DIMENSION : MILLIMETER.
  2. OUTLINE CONFORMS TO EIA-481 & EIA-541.

**Note:** For the most current drawing please refer to IR website at: <http://www.irf.com/package/>

**Notes:**

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Starting  $T_J = 25^\circ\text{C}$ ,  $L = 16\text{mH}$ ,  $R_G = 25\Omega$ ,  $I_{AS} = 4.1\text{A}$ .
- ③ Pulse width  $\leq 400\mu\text{s}$ ; duty cycle  $\leq 2\%$ .
- ④ When mounted on 1 inch square copper board
- ⑤  $C_{oss}$  eff. is a fixed capacitance that gives the same charging time as  $C_{oss}$  while  $V_{DS}$  is rising from 0 to 80%  $V_{DSS}$
- ⑥  $I_{SD} \leq 4.1\text{A}$ ,  $di/dt \leq 210\text{A}/\mu\text{s}$ ,  $V_{DD} \leq V_{(BR)DSS}$ ,  $T_J \leq 150^\circ\text{C}$

**Qualification information<sup>†</sup>**

Qualification level	Industriid (per JEDEC JESD47F <sup>††</sup> guidelines)	
Moisture Sensitivity Level	SO-8	MSL1 (per JEDEC J-STD-020D <sup>††</sup> )
RoHS compliant	Yes	

<sup>†</sup> Qualification standards can be found at International Rectifier's web site: <http://www.irf.com/product-info/reliability>

<sup>††</sup> Applicable version of JEDEC standard at the time of product release

International  
 Rectifier

**IR WORLD HEADQUARTERS:** 101 N. Sepulveda Blvd., El Segundo, California 90245, USA  
 To contact International Rectifier, please visit <http://www.irf.com/whoto-call/>